

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1534	SERIAL NO.
LIST OF ART CITED BY APPLICANT (Use several sheets, if necessary)				APPLICANT Kie Y. Ahn et al.	
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS (including Author, Title, Date, Pertinent Pages, Etc.)					
Examiner Cite					
Initials No. <sup>1</sup>					
TL			YING SHI ET AL., "Tunneling Leakage Current in Ultrathin (<4nm) Nitride/Oxide Stack Dielectrics," 3 pages ( 1998).		
TL			W.-H. LEE ET AL., "A Novel High-k Inter-Poly Dielectric (IPD), Al <sub>2</sub> O <sub>3</sub> for Low Voltage/High speed Flash Memories: Erasing in msec at 3.3V," p. 117-118, ( 1997).		
TL			XIN GUO ET AL., "High Quality Ultra-thin (1.5 nm) TiO <sub>2</sub> /Si <sub>3</sub> N <sub>4</sub> Gate Dielectric for Deep Sub-micron CMOS technology," 4 pages, ( 1999).		
TL			H.F. LUAN ET AL., "High quality Ta <sub>2</sub> O <sub>5</sub> gate dielectrics with T <sub>ox,eq</sub> <10 Å," 4 pages, (1999).		
TL			K.J. HUBBARD <sup>a)</sup> ET AL., "Thermodynamic stability of binary oxides in contact with silicon," p. 2757-2776, ( 1996).		
TL			B. CHENG ET AL., "The Impact of High-k Gate Dielectrics and Metal Gate Electrodes on Sub-100 nm MOSFET's," p. 1537-1544, (1999).		
TL			C.T. LIU, "Circuit Requirement and Integration Challenges of Thin Gate Dielectrics for Ultra Small MOSFETs," 4 pages, ( 1998).		
TL			B.H. LEE ET AL., "Ultrathin Hafnium Oxide with Low Leakage and Excellent Reliability for Alternative Gate Dielectric Application," 4 pages, ( 1999).		
TL			S.P. MURARKA ET AL., "Thermal oxidation of hafnium silicide films on silicon," 3 pages, ( 1980).		
TL			ALBERT CHIN ET AL., "High Quality La <sub>2</sub> O <sub>3</sub> and Al <sub>2</sub> O <sub>3</sub> Gate Dielectric with Equivalent Oxide Thickness 5-10Å," 2 pages, ( 2000).		
TL			D.A. MULLER ET AL., "The electronic structure at the atomic scale of ultrathin gate oxides," 4 pages, ( 1999).		
TL			Y. SAITO ET AL, "High-Integrity Silicon Oxide Grown at Low-Temperature by Atomic Oxygen Generated in High-Density Krypton Plasma," 2 pages, ( 1999).		
EXAMINER			DATE CONSIDERED		
Thao le			20 Feb 02		
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## U.S. PATENT DOCUMENTS

Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
TL	AA	6,020,024	2-1-2000	Maiti et al.			
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
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	AL						

## FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
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	AN							
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